# **NP0080TA Series**

# **Low Capacitance Protector**

The NP series of low voltage/low capacitance overvoltage protection devices protect high speed xDSL line drivers and chipsets from both Lightning Surge and ESD events. The devices are designed with a low nominal capacitance as well as extremely low differential capacitance across frequency and voltage. The inherent low off-state leakage current provides superior performance in low voltage high speed applications. These characteristics allow protection of the system without distortion of the high speed data signal.

With it's advanced silicon structure the NP product is able to clamp very fast ESD events, and crowbar high energy surge events to help protect sensitive IC's all in a small footprint. The convenient flow thru design minimizes trace routing while maximizing circuit performance.

The NP series of low voltage/low capacitance devices helps designers to comply with the various regulatory standards and recommendations including: GR-1089-CORE, IEC 61000-4-5, ITU K.20/K.21/K.45, IEC 60950, TIA-968-A, FCC Part 68, EN 60950, UL 1950.

### Features

- Low Nominal Capacitance
- Extremely Low Differential Capacitance
- Low Leakage (Transparent)
- High Surge Capability
- Precise Clamping Voltage
- Small Package Size
- Bi-directional Operation
- Flow Thru Layout
- IEC 61000-4-2 Level 4 ESD protection
- These are Pb-Free Devices

### **Typical Applications**

- VDSL, ADSL, Access, Central Office, and Customer Premise modems and gateway IC side line driver chipset protection
- 10/100/1000 Ethernet Protection
- RS-232, RS-485 Transceiver Protection

### **ELECTRICAL CHARACTERISTICS**

	V <sub>RWM</sub>	V <sub>BR</sub>	I <sub>R</sub> @ V <sub>R</sub> =V <sub>RWM</sub>	C@ V <sub>R</sub> = 2 V	Δ°C 0 V-V <sub>RWM</sub>
Device	(V)	(V)	(μΑ)	(pF)	(pF)
NP0080TAT1G	8	9.5	0.5	13	4
NP0120TAT1G	12	12.5	0.5	13	3

### SURGE/ESD RATINGS

Waveform	8x20μA	ESD Air	ESD Contact	
Value	50 A	15 kV	6 kV	



### **ON Semiconductor®**

http://onsemi.com

5 1 TSOP-5 TA SUFFIX CASE 483

### MARKING DIAGRAM



(Note: Microdot may be in either location)

**PIN CONNECTIONS** 



### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

## NP0080TA Series

Symbol	Rating		Min	Тур	Max	Unit
V <sub>RWM</sub>	Repetitive peak off-state voltage: Rated maximum	NP0080TAT1G			±8	V
(peak) continuous voltage that may be applied off-state condition		NP0120TAT1G			±12	
	Breakdown Voltage: The minimum voltage across the	NP0080TAT1G	9.5			V
	device in or at the breakdown region. Measured at I <sub>BR</sub> = 1 mA	NP0120TAT1G	12.5			
	Breakover Voltage: The maximum voltage across the	NP0080TAT1G			20	V
	device in or at the breakover region. Measured at $I_{(BO)}=800\mbox{ mA}$	NP0120TAT1G			30	
I <sub>R</sub>	<b>Off-state Current</b> : The dc value of current that results from the application of the off-state voltage				0.5	μΑ
Ι <sub>Η</sub>	Holding Current: The minimum current required to maintain the device in the on-state.			50		mA
	<b>Off-State Capacitance</b> : f = 1.0 MHz, V <sub>d</sub> = 1.0 Vrms,	NP0080TAT1G			13	pF
	$V_{\rm D} = -2  \rm Vdc$	NP0120TAT1G			13	
$\Delta C_1$	$\Delta \text{ Capacitance: } f = 1.0 \text{ MHz}, V_d = 1.0 \text{ Vrms}, V_D =   0 \text{ V} - \text{Vrwm}  $	NP0080TAT1G		4		pF
	$v_{\rm D} =  0 v - v_{\rm Will} $	NP0120TAT1G		3		
IPPS	Peak Pulse Current: Rated maximum value of peak impulse pulse current that may be applied. 8x20 $\mu s,$ IEC $-61000-4-5$		50			A
Rated maximum v	Electrostatic Discharge (CONTACT): Rated maximum value of ESD per IEC-61000-4-2	NP0080TAT1G		8		kV
		NP0120TAT1G		6		
	Electrostatic Discharge (AIR): Rated maximum value of ESD per IEC-61000-4-2			15		
T <sub>STG</sub>	Storage Temperature Range		-55		+150	°C
TJ	Operating Junction Temperature Range		-40		+125	°C

## **ELECTRICAL CHARACTERISTICS TABLE** (T<sub>A</sub> = 25°C unless otherwise noted)

Symbol	Parameter	
V <sub>RWM</sub>	Repetitive peak off-state voltage	
V <sub>BR</sub>	Breakdown voltage	
V <sub>(BO)</sub>	Breakover voltage	
I <sub>R</sub>	Off-state current	
Ι <sub>Η</sub>	Holding current	



### **Application Information**

The NPXXXXTAT can be used after the isolation transformer as protection for the xDSL line driver. The devices can be configured to protect against both differential and common mode surges and ESD.



### NP0080TA Series

### **DEVICE ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
NP0080TAT1G	TSOP-5 (Pb-Free)	3000 / Tape & Reel
NP0120TAT1G	TSOP-5 (Pb-Free)	3000 / Tape & Reel

†For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

### PACKAGE DIMENSIONS

TSOP-5 CASE 483-02 ISSUE H









NOTES: 1. DIMENSIONING AND TOLERANCING PER

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  CONTROLLING DIMENSION: MILLIMETERS.
- CONTROLLING DIMENSION: MILLINE FEAS 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.
- 5 OPTIONAL CONSTRUCTION: AN ADDITIONAL TRIMMED LEAD IS ALLOWED IN THIS LOCATION. TRIMMED LEAD NOT TO EXTEND MORE THAN 0.2 FROM BODY.

	MILLIMETERS		
DIM	MIN	MAX	
Α	3.00 BSC		
в	1.50 BSC		
С	0.90	1.10	
D	0.25	0.50	
G	0.95 BSC		
н	0.01	0.10	
J	0.10	0.26	
К	0.20	0.60	
L	1.25	1.55	
м	0 °	10 °	
S	2.50	3.00	

### SOLDERING FOOTPRINT\*



\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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